Infineon Technologies - XC2797X200F100LABKXUMA1 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	C166SV2
Core Size	16/32-Bit
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	150
Program Memory Size	1.6MB (1.6M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	138K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 30x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-176-12
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xc2797x200f100labkxuma1

16/32-Bit

Architecture

XC2797X

16/32-Bit Single-Chip Microcontroller
with 32-Bit Performance
XC2000 Family / High Line

Data Sheet

V1.3 2011-07

Microcontrollers

16/32-Bit Single-Chip Microcontroller with 32-Bit Performance

XC2797X (XC2000 Family)

1 Summary of Features

For a quick overview and easy reference, the features of the XC2797X are summarized here.

- High-performance CPU with five-stage pipeline and MPU
  - 10 ns instruction cycle @ 100 MHz CPU clock (single-cycle execution)
  - One-cycle 32-bit addition and subtraction with 40-bit result
  - One-cycle multiplication (16 × 16 bit)
  - Background division (32 / 16 bit) in 21 cycles
  - One-cycle multiply-and-accumulate (MAC) instructions
  - Enhanced Boolean bit manipulation facilities
  - Zero-cycle jump execution
  - Additional instructions to support HLL and operating systems
  - Register-based design with multiple variable register banks
  - Fast context switching support with two additional local register banks
  - 16 Mbytes total linear address space for code and data
  - 1,024 Bytes on-chip special function register area (C166 Family compatible)
  - Integrated Memory Protection Unit (MPU)
- Interrupt system with 16 priority levels providing 112 interrupt nodes
  - Selectable external inputs for interrupt generation and wake-up
  - Fastest sample-rate 10 ns
- Eight-channel interrupt-driven single-cycle data transfer with Peripheral Event Controller (PEC), 24-bit pointers cover total address space
- Clock generation from internal or external clock sources, using on-chip PLL or prescaler
- Hardware CRC-Checker with Programmable Polynomial to Supervise On-Chip Memory Areas
- On-chip memory modules
  - 8 Kbytes on-chip stand-by RAM (SBRAM)
  - 2 Kbytes on-chip dual-port RAM (DPRAM)
  - 24 Kbytes on-chip data SRAM (DSRAM)
  - Up to 112 Kbytes on-chip program/data SRAM (PSRAM)
  - Up to 1600 Kbytes on-chip program memory (Flash memory)
  - Memory content protection through Error Correction Code (ECC)

1.1 Basic Device Types

Basic device types are available and can be ordered through Infineon's direct and/or distribution channels.

Table 1 Synopsis of XC2797X Basic Device Types

Derivative[1]	Flash Memory[2]	PSRAM[3]	Capt./Comp. Modules	ADC[4] Chan.	Interfaces[4]
XC2797X-200FxL	1,600 Kbytes	112 Kbytes	CC1/2 CCU60/1/2/3	16 + 14	2 CAN Nodes, 6 Serial Chan.

1) x is a placeholder for available speed grade in MHz. Can be 100 only.
2) Specific information about the on-chip Flash memory in **Table 3** and **Table 4**.
3) All derivatives additionally provide 8 Kbytes SBRAM, 2 Kbytes DPRAM, and 24 Kbytes DSRAM.
4) Specific information about the available channels in **Table 5**.
Analog input channels are listed for each Analog/Digital Converter module separately (ADC0 + ADC1).

1.2 Special Device Types

Special device types are only available for high-volume applications on request.

Table 2 Synopsis of XC2797X Special Device Types

Derivative[1]	Flash Memory[2]	PSRAM[3]	Capt./Comp. Modules	ADC[4] Chan.	Interfaces[4]
XC2797X-136FxL	1,088 Kbytes	80 Kbytes	CC1/2 CCU60/1/2/3	16 + 14	2 CAN Nodes 6 Serial Chan.

1) x is a placeholder for available speed grade in MHz. Can be 80 or 100.
2) Specific information about the on-chip Flash memory in **Table 3** and **Table 4**.
3) All derivatives additionally provide 8 Kbytes SBRAM, 2 Kbytes DPRAM, and 24 Kbytes DSRAM.
4) Specific information about the available channels in **Table 5**.
Analog input channels are listed for each Analog/Digital Converter module separately (ADC0 + ADC1).

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
91	P0.0	O0 / I	St/B	**Bit 0 of Port 0, General Purpose Input/Output**
	U1C0_DOUT	O1	St/B	**USIC1 Channel 0 Shift Data Output**
	CCU61_CC60	O3	St/B	**CCU61 Channel 0 IOutput**
	A0	OH	St/B	**External Bus Interface Address Line 0**
	U1C0_DX0A	I	St/B	**USIC1 Channel 0 Shift Data Input**
	CCU61_CC60INA	I	St/B	**CCU61 Channel 0 Input**
	ESR1_11	I	St/B	**ESR1 Trigger Input 11**
92	P4.5	O0 / I	St/B	**Bit 5 of Port 4, General Purpose Input/Output**
	U3C0_DOUT	O1	St/B	**USIC3 Channel 0 Shift Data Output**
	CC2_CC29	O3 / I	St/B	**CAPCOM2 CC29IO Capture Inp./Compare Out.**
	CCU61_CCPOS0A	I	St/B	**CCU61 Position Input 0**
	U3C0_DX0B	I	St/B	**USIC3 Channel 0 Shift Data Input**
	ESR2_10	I	St/B	**ESR2 Trigger Input 10**
93	P4.6	O0 / I	St/B	**Bit 6 of Port 4, General Purpose Input/Output**
	U3C0_DOUT	O1	St/B	**USIC3 Channel 0 Shift Data Output**
	CC2_CC30	O3 / I	St/B	**CAPCOM2 CC30IO Capture Inp./ Compare Out.**
	T4INA	I	St/B	**GPT12E Timer T4 Count/Gate Input**
	CCU61_CCPOS1A	I	St/B	**CCU61 Position Input 1**
94	P2.7	O0 / I	St/B	**Bit 7 of Port 2, General Purpose Input/Output**
	U0C1_SELO0	O1	St/B	**USIC0 Channel 1 Select/Control 0 Output**
	U0C0_SELO1	O2	St/B	**USIC0 Channel 0 Select/Control 1 Output**
	CC2_CC20	O3 / I	St/B	**CAPCOM2 CC20IO Capture Inp./ Compare Out.**
	A20	OH	St/B	**External Bus Interface Address Line 20**
	U0C1_DX2C	I	St/B	**USIC0 Channel 1 Shift Control Input**
	RxDC1C	I	St/B	**CAN Node 1 Receive Data Input**
	ESR2_7	I	St/B	**ESR2 Trigger Input 7**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
110	P0.4	O0 / I	St/B	**Bit 4 of Port 0, General Purpose Input/Output**
	U1C1_SELO 0	O1	St/B	**USIC1 Channel 1 Select/Control 0 Output**
	U1C0_SELO 1	O2	St/B	**USIC1 Channel 0 Select/Control 1 Output**
	CCU61_COU T61	O3	St/B	**CCU61 Channel 1 Output**
	A4	OH	St/B	**External Bus Interface Address Line 4**
	U1C1_DX2A	I	St/B	**USIC1 Channel 1 Shift Control Input**
	RxDC1B	I	St/B	**CAN Node 1 Receive Data Input**
	ESR2_8	I	St/B	**ESR2 Trigger Input 8**
112	P2.13	O0 / I	St/B	**Bit 13 of Port 2, General Purpose Input/Output**
	U2C1_SELO 2	O1	St/B	**USIC2 Channel 1 Select/Control 2 Output**
113	P3.2	O0 / I	St/B	**Bit 2 of Port 3, General Purpose Input/Output**
	U2C0_SCLK OUT	O1	St/B	**USIC2 Channel 0 Shift Clock Output**
	U2C0_DX1B	I	St/B	**USIC2 Channel 0 Shift Clock Input**
114	P12.3	O0 / I	St/B	**Bit 3 of Port 12, General Purpose Input/Output**
	CC1_CC3	O1 / I	St/B	**CAPCOM1 CC3IO Capture Inp./ Compare Out.**
115	P2.10	O0 / I	St/B	**Bit 10 of Port 2, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	U0C0_SELO 3	O2	St/B	**USIC0 Channel 0 Select/Control 3 Output**
	CC2_CC23	O3 / I	St/B	**CAPCOM2 CC23IO Capture Inp./ Compare Out.**
	A23	OH	St/B	**External Bus Interface Address Line 23**
	U0C1_DX0E	I	St/B	**USIC0 Channel 1 Shift Data Input**
	CAPINA	I	St/B	**GPT12E Register CAPREL Capture Input**
	U3C1_DX0A	I	St/B	**USIC3 Channel 1 Shift Data Input**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
128	P3.6	O0 / I	St/B	**Bit 6 of Port 3, General Purpose Input/Output**
	U2C1_DOUT	O1	St/B	**USIC2 Channel 1 Shift Data Output**
	U0C0_SELO 6	O3	St/B	**USIC0 Channel 0 Select/Control 6 Output**
	U2C1_DX0A	I	St/B	**USIC2 Channel 1 Shift Data Input**
	U2C1_DX1B	I	St/B	**USIC2 Channel 1 Shift Clock Input**
129	P10.7	O0 / I	St/B	**Bit 7 of Port 10, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	CCU60_COU T63	O2	St/B	**CCU60 Channel 3 Output**
	AD7	OH / IH	St/B	**External Bus Interface Address/Data Line 7**
	U0C1_DX0B	I	St/B	**USIC0 Channel 1 Shift Data Input**
	CCU60_CCP OS0A	I	St/B	**CCU60 Position Input 0**
	T4INB	I	St/B	**GPT12E Timer T4 Count/Gate Input**
130	P0.7	O0 / I	St/B	**Bit 7 of Port 0, General Purpose Input/Output**
	U1C1_DOUT	O1	St/B	**USIC1 Channel 1 Shift Data Output**
	U1C0_SELO 3	O2	St/B	**USIC1 Channel 0 Select/Control 3 Output**
	A7	OH	St/B	**External Bus Interface Address Line 7**
	U1C1_DX0B	I	St/B	**USIC1 Channel 1 Shift Data Input**
	CCU61_CTR APB	I	St/B	**CCU61 Emergency Trap Input**
131	P3.7	O0 / I	St/B	**Bit 7 of Port 3, General Purpose Input/Output**
	U2C1_DOUT	O1	St/B	**USIC2 Channel 1 Shift Data Output**
	U2C0_SELO 3	O2	St/B	**USIC2 Channel 0 Select/Control 3 Output**
	U0C0_SELO 7	O3	St/B	**USIC0 Channel 0 Select/Control 7 Output**
	U2C1_DX0B	I	St/B	**USIC2 Channel 1 Shift Data Input**

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
152	P13.3	O0 / I	St/B	**Bit 3 of Port 13, General Purpose Input/Output**
	CC1_CC11	O1 / I	St/B	**CAPCOM1 CC11IO Capture Inp./ Compare Out.**
	CCU60_CC60	O2	St/B	**CCU60 Channel 0 Output**
	TMS_E	IH	St/B	**JTAG Test Mode Selection Input**
	CCU60_CC60INC	I	St/B	**CCU60 Channel 0 Input**
153	P9.4	O0 / I	St/B	**Bit 4 of Port 9, General Purpose Input/Output**
	CCU63_COUT61	O1	St/B	**CCU63 Channel 1 Output**
	U2C0_DOUT	O2	St/B	**USIC2 Channel 0 Shift Data Output**
	CCU62_COUT63	O3	St/B	**CCU62 Channel 3 Output**
154	P9.5	O0 / I	St/B	**Bit 5 of Port 9, General Purpose Input/Output**
	CCU63_COUT62	O1	St/B	**CCU63 Channel 2 Output**
	U2C0_DOUT	O2	St/B	**USIC2 Channel 0 Shift Data Output**
	CCU62_COUT62	O3	St/B	**CCU62 Channel 2 Output**
	U2C0_DX0E	I	St/B	**USIC2 Channel 0 Shift Data Input**
	CCU60_CCPOS2B	I	St/B	**CCU60 Position Input 2**
156	P10.14	O0 / I	St/B	**Bit 14 of Port 10, General Purpose Input/Output**
	U1C0_SELO1	O1	St/B	**USIC1 Channel 0 Select/Control 1 Output**
	U0C1_DOUT	O2	St/B	**USIC0 Channel 1 Shift Data Output**
	U3C0_SCLKOUT	O3	St/B	**USIC3 Channel 0 Shift Clock Output**
	$\overline{RD}$	OH	St/B	**External Bus Interface Read Strobe Output**
	ESR2_2	I	St/B	**ESR2 Trigger Input 2**
	U0C1_DX0C	I	St/B	**USIC0 Channel 1 Shift Data Input**
	U3C0_DX1A	I	St/B	**USIC3 Channel 0 Shift Clock Input**

Table 8 XC2797X Memory Map (cont'd)[1)]

Address Area	Start Loc.	End Loc.	Area Size[2)]	Notes
Reserved for DPRAM	$00'F200_H$	$00'F5FF_H$	1 Kbytes	
ESFR area	$00'F000_H$	$00'F1FF_H$	0.5 Kbytes	
XSFR area	$00'E000_H$	$00'EFFF_H$	4 Kbytes	
Data SRAM (DSRAM)	$00'8000_H$	$00'DFFF_H$	24 Kbytes	
External memory area	$00'0000_H$	$00'7FFF_H$	32 Kbytes	

1) Accesses to the shaded areas are reserved. In devices with external bus interface these accesses generate external bus accesses.

2) The areas marked with "<" are slightly smaller than indicated, see column "Notes".

3) The uppermost 4-Kbyte sector of the first Flash segment is reserved for internal use ($C0'F000_H$ to $C0'FFFF_H$).

4) Several pipeline optimizations are not active within the external IO area. This is necessary to control external peripherals properly.

This common memory space consists of 16 Mbytes organized as 256 segments of 64 Kbytes; each segment contains four data pages of 16 Kbytes. The entire memory space can be accessed bytewise or wordwise. Portions of the on-chip DPRAM and the register spaces (ESFR/SFR) additionally are directly bit addressable.

The internal data memory areas and the Special Function Register areas (SFR and ESFR) are mapped into segment 0, the system segment.

The Program Management Unit (PMU) handles all code fetches and, therefore, controls access to the program memories such as Flash memory and PSRAM.

The Data Management Unit (DMU) handles all data transfers and, therefore, controls access to the DSRAM and the on-chip peripherals.

Both units (PMU and DMU) are connected to the high-speed system bus so that they can exchange data. This is required if operands are read from program memory, code or data is written to the PSRAM, code is fetched from external memory, or data is read from or written to external resources. These include peripherals on the LXBus such as USIC or MultiCAN. The system bus allows concurrent two-way communication for maximum transfer performance.

Up to 112 Kbytes of on-chip Program SRAM (PSRAM) are provided to store user code or data. The PSRAM is accessed via the PMU and is optimized for code fetches. A section of the PSRAM with programmable size can be write-protected.

Note: The actual size of the PSRAM depends on the quoted device type.

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).
The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.
The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.

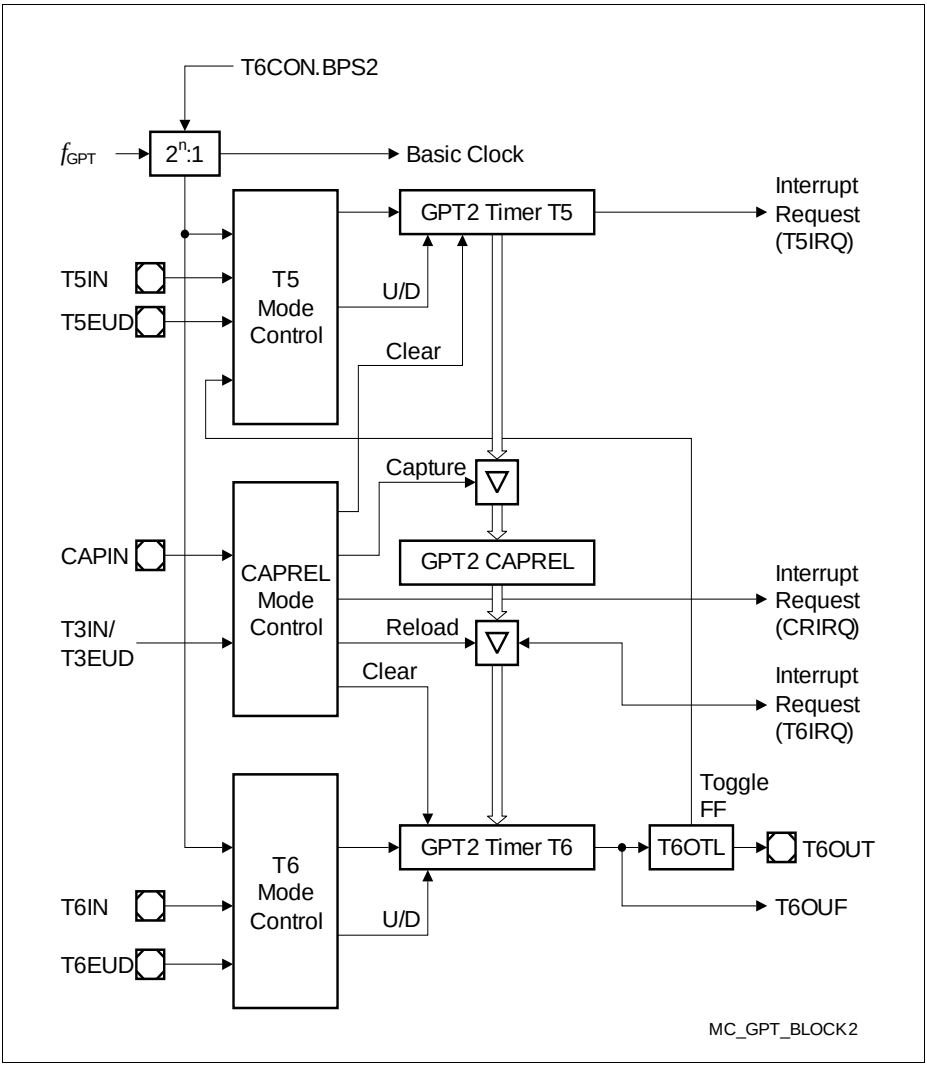

Figure 9 Block Diagram of GPT2

Table 13 Operating Conditions (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Overload current coupling factor for digital I/O pins	K_{OVD} CC	–	1.0 x 10^{-2}	3.0 x 10^{-2}		I_{OV}< 0 mA; not subject to production test
		–	1.0 x 10^{-4}	5.0 x 10^{-3}		I_{OV}> 0 mA; not subject to production test
Absolute sum of overload currents	$\Sigma\|I_{OV}\|$ SR	–	–	50	mA	not subject to production test
Digital core supply voltage for domain M[8)]	V_{DDIM} CC	–	1.5	–		
Digital core supply voltage for domain 1[8)]	V_{DDI1} CC	–	1.5	–		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	3.0	–	5.5	V	
Digital ground voltage	V_{SS} SR	–	0	–	V	

1) To ensure the stability of the voltage regulators the EVRs must be buffered with ceramic capacitors. Separate buffer capacitors with the recomended values shall be connected as close as possible to each V_{DDIM} and V_{DDI1} pin to keep the resistance of the board tracks below 2 Ohm. Connect all V_{DDI1} pins together. The minimum capacitance value is required for proper operation under all conditions (e.g. temperature). Higher values slightly increase the startup time.

2) Use one Capacitor for each pin.

3) This is the reference load. For bigger capacitive loads, use the derating factors listed in the PAD properties section.

4) The timing is valid for pin drivers operating in default current mode (selected after reset). Reducing the output current may lead to increased delays or reduced driving capability (C_L).

5) The operating frequency range may be reduced for specific device types. This is indicated in the device designation (...FxxL). 80 MHz devices are marked ...F80L.

6) Overload conditions occur if the standard operating conditions are exceeded, i.e. the voltage on any pin exceeds the specified range: $V_{OV} > V_{IHmax}$ ($I_{OV} > 0$) or $V_{OV} < V_{ILmin}$ (($I_{OV} < 0$). The absolute sum of input overload currents on all pins may not exceed 50 mA. The supply voltages must remain within the specified limits. Proper operation under overload conditions depends on the application. Overload conditions must not occur on pin XTAL1 (powered by V_{DDIM}).

7) An overload current (I_{OV}) through a pin injects a certain error current (I_{INJ}) into the adjacent pins. This error current adds to the respective pins leakage current (I_{OZ}). The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV}. The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it.The total current through a pin is $|I_{TOT}| = |I_{OZ}| + (|I_{OV}| \ K_{OV})$. The additional error current may distort the input voltage on analog inputs.
8) Value is controlled by on-chip regulator

4.3 DC Parameters

These parameters are static or average values that may be exceeded during switching transitions (e.g. output current).

The XC2797X can operate within a wide supply voltage range from 3.0 V to 5.5 V. However, during operation this supply voltage must remain within 10 percent of the selected nominal supply voltage. It cannot vary across the full operating voltage range.

Because of the supply voltage restriction and because electrical behavior depends on the supply voltage, the parameters are specified separately for the upper and the lower voltage range.

During operation, the supply voltages may only change with a maximum speed of dV/dt < 1 V/ms.

Leakage current is strongly dependent on the operating temperature and the voltage level at the respective pin. The maximum values in the following tables apply under worst case conditions, i.e. maximum temperature and an input level equal to the supply voltage.
The value for the leakage current in an application can be determined by using the respective leakage derating formula (see tables) with values from that application.

The pads of the XC2797X are designed to operate in various driver modes. The DC parameter specifications refer to the pad current limits specified in **Section 4.7.4**.

Table 16 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output High voltage[7]	V_{OH} CC	V_{DDP} - 1.0	–	–	V	$I_{OH} \geq I_{OHmax}$
		V_{DDP} - 0.4	–	–	V	$I_{OH} \geq I_{OHnom}$ [8]
Output Low Voltage[7]	V_{OL} CC	–	–	0.4	V	$I_{OL} \leq I_{OLnom}$ [9]
		–	–	1.0	V	$I_{OL} \leq I_{OLmax}$

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device.

6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level.

7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

8) As a rule, with decreasing output current the output levels approach the respective supply level (VOL->VSS, VOH->VDDP). However, only the levels for nominal output currents are verified.

9) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

1) The supply current caused by leakage depends mainly on the junction temperature and the supply voltage. The temperature difference between the junction temperature T_J and the ambient temperature T_A must be taken into account. As this fraction of the supply current does not depend on device activity, it must be added to other power consumption values.
2) All inputs (including pins configured as inputs) are set at 0 V to 0.1 V or at V_{DDP} - 0.1 V to V_{DDP} and all outputs (including pins configured as outputs) are disconnected.

Note: A fraction of the leakage current flows through domain DMP_A (pin V_{DDPA}). This current can be calculated as 7,000 $\times e^{-\alpha}$, with α = 5000 / (273 + 1.3 $\times T_J$). For T_J = 150°C, this results in a current of 160 μA.

The leakage power consumption can be calculated according to the following formulas:

$I_{LK1} = 600{,}000 \times e^{-\alpha}$ with $\alpha = 5000 / (273 + B \times T_J)$

Parameter B must be replaced by

- 1.1 for typical values
- 1.4 for maximum values

Table 20 ADC Parameters (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Broken wire detection delay against VAGND[1]	t_{BWG} CC	–	–	50[2]		
Broken wire detection delay against VAREF[1]	t_{BWR} CC	–	–	50[3]		
Conversion time for 8-bit result[1]	t_{c8} CC	(11 + *STC*) x t_{ADCI} + 2 x t_{SYS}	–	–		
Conversion time for 10-bit result[1]	t_{c10} CC	(13 + *STC*) x t_{ADCI} + 2 x t_{SYS}	–	–		
Total Unadjusted Error	|TUE| CC	–	1	2	LSB	[4]
Wakeup time from analog powerdown, fast mode	t_{WAF} CC	–	–	4	µs	
Wakeup time from analog powerdown, slow mode	t_{WAS} CC	–	–	15	µs	
Analog reference ground	V_{AGND} SR	V_{SS} - 0.05	–	1.5	V	
Analog input voltage range	V_{AIN} SR	V_{AGND}	–	V_{AREF}	V	[5]
Analog reference voltage	V_{AREF} SR	V_{AGND} + 1.0	–	V_{DDPA} + 0.05	V	

1) This parameter includes the sample time (also the additional sample time specified by STC), the time to determine the digital result and the time to load the result register with the conversion result. Values for the basic clock t_{ADCI} depend on programming.

2) The broken wire detection delay against V_{AGND} is measured in numbers of consecutive precharge cycles at a conversion rate of not more than 500 µs. Result below 10% (66_H)

3) The broken wire detection delay against V_{AREF} is measured in numbers of consecutive precharge cycles at a conversion rate of not more than 10 µs. This function is influenced by leakage current, in particular at high temperature. Result above 80% (332_H)

Table 26 System PLL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VCO output frequency	f_{VCO} CC	50	–	110	MHz	*VCOSEL*= 00b; *VCOmode*= controlled
		10	–	40	MHz	*VCOSEL*= 00b; *VCOmode*= free running
		100	–	200	MHz	*VCOSEL*= 01b; *VCOmode*= controlled
		20	–	80	MHz	*VCOSEL*= 01b; *VCOmode*= free running

4.7.2.2 Wakeup Clock

When wakeup operation is selected (SYSCON0.CLKSEL = 00_B), the system clock is derived from the low-frequency wakeup clock source:

$f_{SYS} = f_{WU}$.

In this mode, a basic functionality can be maintained without requiring an external clock source and while minimizing the power consumption.

4.7.2.3 Selecting and Changing the Operating Frequency

When selecting a clock source and the clock generation method, the required parameters must be carefully written to the respective bit fields, to avoid unintended intermediate states.

Many applications change the frequency of the system clock (f_{SYS}) during operation in order to optimize system performance and power consumption. Changing the operating frequency also changes the switching currents, which influences the power supply.

To ensure proper operation of the on-chip EVRs while they generate the core voltage, the operating frequency shall only be changed in certain steps. This prevents overshoots and undershoots of the supply voltage.

To avoid the indicated problems, recommended sequences are provided which ensure the intended operation of the clock system interacting with the power system.
Please refer to the Programmer's Guide.

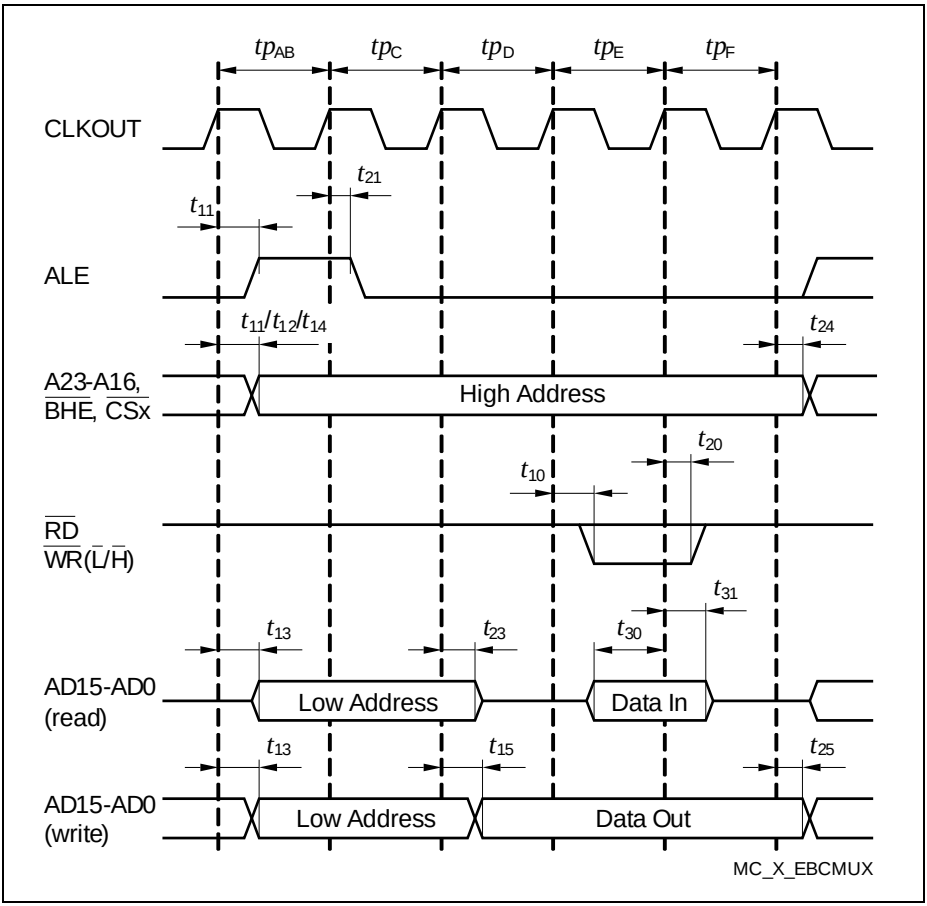

Figure 23 Multiplexed Bus Cycle

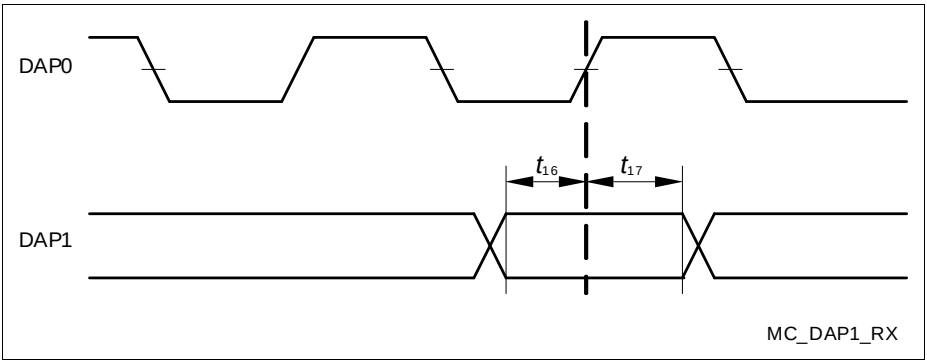

Figure 28 DAP Timing Host to Device

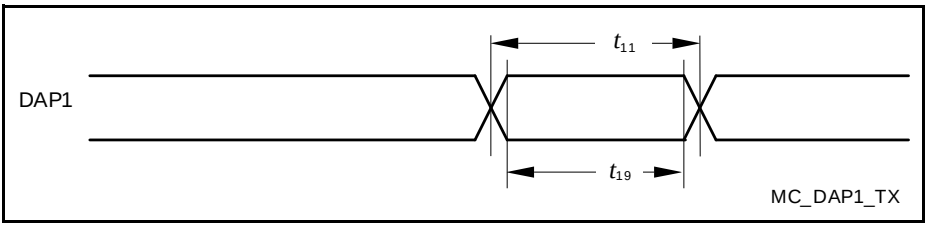

Figure 29 DAP Timing Device to Host

Note: The transmission timing is determined by the receiving debugger by evaluating the sync-request synchronization pattern telegram.

Debug via JTAG

The following parameters are applicable for communication through the JTAG debug interface. The JTAG module is fully compliant with IEEE1149.1-2000.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 40 is valid under the following conditions: C_L= 20 pF; voltage_range= upper

Table 40 JTAG Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50	–	–	ns	[1]
TCK high time	t_2 SR	16	–	–	ns	

Table 41 JTAG Interface Timing for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TDI/TMS hold after TCK rising edge	t_7 SR	6	–	–	ns	
TDO valid from TCK falling edge (propagation delay)[1]	t_8 CC	–	32	36	ns	
TDO high impedance to valid output from TCK falling edge[2][1]	t_9 CC	–	32	36	ns	
TDO valid output to high impedance from TCK falling edge[1]	t_{10} CC	–	32	36	ns	
TDO hold after TCK falling edge[1]	t_{18} CC	5	–	–	ns	

1) The falling edge on TCK is used to generate the TDO timing.

2) The setup time for TDO is given implicitly by the TCK cycle time.

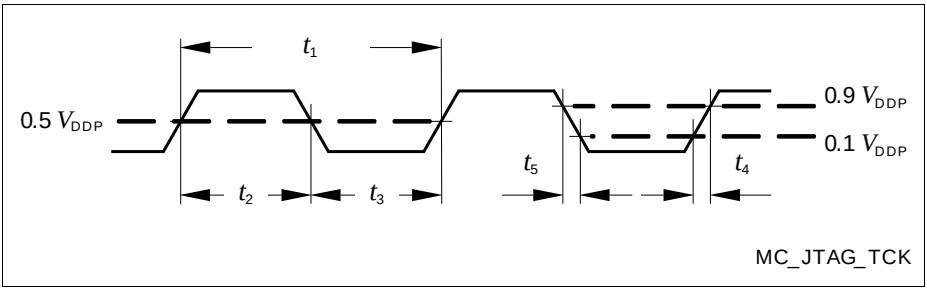

Figure 30 Test Clock Timing (TCK)